	Application No.	Applicant(s)
į	10/613,064	KWEON, YOUNG-CHAN
Notice of Allowability	Examiner	Art Unit
	Laura M. Schillinger	2813
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. This communication is responsive to 3/21/05.		
2. ☑ The allowed claim(s) is/are 16-22, 38-41, 53-62.		
3. A The drawings filed on 07 July 2003 are accepted by the Examiner.		
 4.		
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 2/28/05 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Summar Paper No./Mail Da 8), 7. ⊠ Examiner's Amend	ate

DETAILED ACTION

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

IN THE SPECIFICATION

Please amend the paragraph beginning on page 1, line 4 as follows:

Notice: More than one reissue application has been filed for the reissue of Patent No. 5,81 1,318.

The present reissue application is a continuation of reissue application no. 09/667.643, which is a reissue of Patent No. 5,811,318.

Cancel claims 50-52.

Please add/revive the following claims as required by the rejoinder made below:

53. A TFT substrate. comprising:

a gate electrode comprising at least a refractory metal film formed over a first portion of a substrate:

Application/Control Number: 10/613,064

Art Unit: 2813

a gate pad comprising the refractory metal film formed on a second portion of a substrate: an insulated film formed over the gate electrode and having an exposed area corresponding to the refractory metal film of the gate pad:

<u>a semiconductor film pattern formed over the insulated film: a source electrode formed over a first portion of the semiconductor film pattern;</u>

a drain electrode formed over a second portion of the semiconductor film pattern;

a passivation film pattern formed over the source electrode, having a contact hole over the drain electrode and having an exposed area corresponding to the refractory metal film of the gate pad; a first pixel electrode pattern electrically contacted to the drain electrode on the passivation film pattern: and a second pixel electrode electrically contacted to the exposed area of the refractory metal film of the gate pad.

- 54. A TFT substrate as recited in claim 53, wherein the refractory metal film comprises a material selected from the group consisting of Cr. Ta. Mo. and Ti.
- 55. A TFT substrate as recited in claim 53, further comprising a second metal film formed on the refractory metal film over the first portion of the substrate and formed on the refractory metal film of the gate pad except for the exposed area thereof.
- 56. A TFT substrate as recited in claim 53, wherein the second metal film comprises A1 or A1 alloy.

Application/Control Number: 10/613,064

Art Unit: 2813

57. A TFT substrate as recited in claim 53, wherein the insulated film comprises a nitride film

Page 4

SiN.

58. A TFT substrate as recited in claim 53, wherein the first and second pixel patterns comprise

ITO.

59. A TFT substrate as in claim 53, wherein at least one of the first and the second metal film of

the gate electrode and the gate pad has tapered-sidewalls.

60. A TFT substrate as in claim 59, wherein the second metal film has tapered sidewalls.

61. A TFT substrate as in claim 53, wherein the semiconductor film pattern comprises: an

amorphous silicon film on the insulated film; and

a doped amorphous silicon film on the amorphous silicon film.

62. A TFT substrate as recite in claim 53, wherein the second pixel electrode pattern contacts

portions of the exposed gate pad.

Allowable Subject Matter

29)

Claims 16-22, 38-41, and 53-62 are allowed.

The following is an examiner's statement of reasons for allowance:

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Application/Control Number: 10/613,064

Art Unit: 2813

Applicant's arguments regarding the rejection of claim 16 dated 3/21/05 are considered persuasive and consequently claim 16 contains allowable subject matter. The remaining claims act only to further narrow independent claim 16 and are therefore also deemed to be allowable over prior art. Claims 23-28 and 42-45 are considered an obvious variant of allowed claim 16 and is therefore rejoined as claims 53-62 and also deemed to contain allowable subject matter.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Art Unit: 2813

4/15/05

Laura M Schillinger Primary Examiner Art Unit 2813